

# DFM300BXS12-A000

## Fast Recovery Diode Module

PDS5724-1.3 October 2007 (LN25576)

1200V

## FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Voltage Drop
- Isolated Base

## **APPLICATIONS**

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Snubber Circuits
- Resonant Converters
- Multi-level Switch Inverters

The DFM300BXS12-A000 is a single 1200V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation making the device suitable for the latest drive designs employing pwm and high frequency switching.

These modules incorporates electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sink for safety.

## **ORDERING INFORMATION**

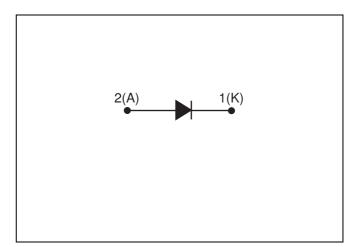
Order As:

#### DFM300BXS12-A000

Note: When ordering, please use the whole part number.

KEY	PARA	NEI	ERS	
V <sub>RRM</sub>				
▼ RRM				

(typ)	2.0 V
(max)	300A
(max)	600A
	(max)



#### Fig. 1 Circuit diagram

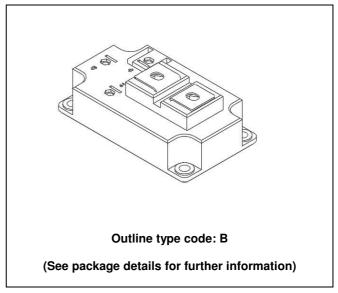


Fig. 2 Module outline



## **ABSOLUTE MAXIMUM RATINGS - PER ARM**

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

#### Tcase = 25° C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>RRM</sub>	Repetitive peak reverse voltage	$T_j = 125^{\circ} C$	1200	V
IF	Forward current (per arm)	DC, $T_{case} = 70 \degree C$ , $T_j = 125 \degree C$	300	А
I <sub>FM</sub>	Max. forward current	$T_{case} = 110 \circ C$ , $t_p = 1ms$	600	А
I <sub>FSM</sub>	Surge (non repetitive) forward current		2236	А
l <sup>2</sup> t	I <sup>2</sup> t value fuse current rating	$V_{R} = 0, t_{P} = 10ms, T_{j} = 125 ^{\circ}C$	25	kA <sup>2</sup> s
P <sub>max</sub>	Maximum power dissipation	$T_{case} = 25 ^{\circ} C, T_{j} = 125 ^{\circ} C$	1.0	kW
V <sub>isol</sub>	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2.5	kV

#### THERMAL AND MECHANICAL RATINGS

$AI_2O_3$
Copper
20mm
11mm
175

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
$R_{th(j-c)}$	Thermal resistance – diode (per arm)	Continuous dissipation – junction to case	-	-	100	° C/kW
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	15	° C/kW
Tj	Junction temperature	-	-	-	125	°C
T <sub>stg</sub>	Storage temperature range	-	-40	-	125	°C
-	Screw torque	Mounting – M6	3	-	5	Nm
		Electrical connections – M6	2.5	-	5	Nm

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures



## STATIC ELECTRICAL CHARACTERISTICS

## $T_j = 25^{\circ} C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
I <sub>RM</sub>	Peak reverse current	$V_{R} = 1200V, T_{j} = 125 ^{\circ}C$	-	-	8	mA
V <sub>F</sub> Forw	Forward voltage	I <sub>F</sub> = 300A	-	2.0	2.5	V
	orward voltage	I <sub>F</sub> = 300A, T <sub>j</sub> = 125°C	-	2.05	2.55	V
L	Inductance (module)	-	-	16	-	nH

#### DYNAMIC ELECTRICAL CHARACTERISTICS

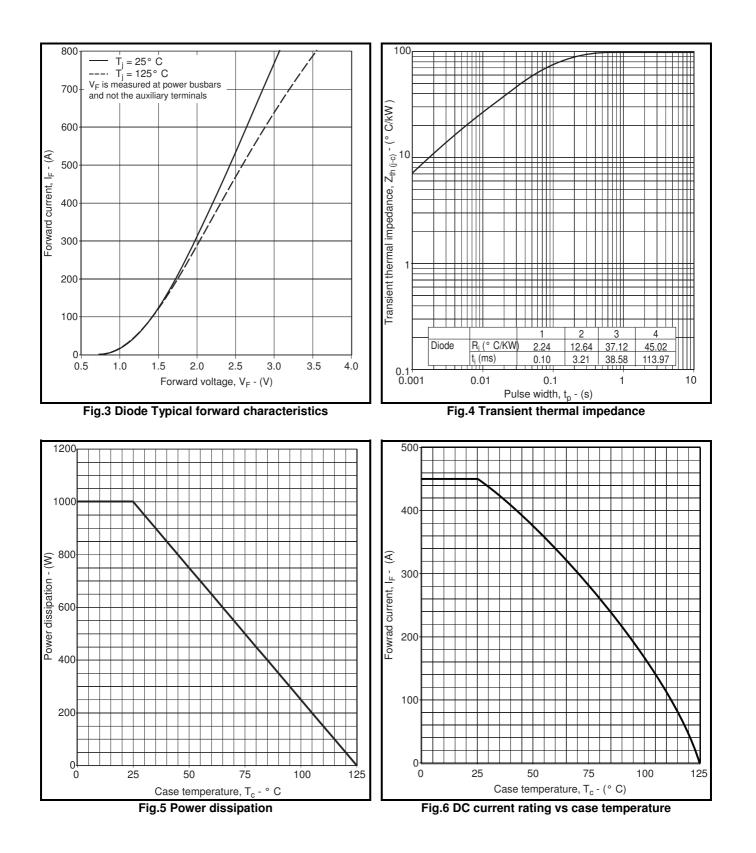
## $T_j = 25^{\circ} C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
t <sub>rr</sub>	Reverse recovery time	I <sub>F</sub> = 300A, dI <sub>F</sub> /dt = 2250A/μs, V <sub>R</sub> = 600V	-	0.4	-	μs
l <sub>rr</sub>	Reverse recovery current		-	300	-	А
Qrr	Reverse recovery charge		-	55	-	μC
E <sub>rec</sub>	Reverse recovery energy		-	17	-	mJ

## $T_j = 125^{\circ}$ C unless stated otherwise.

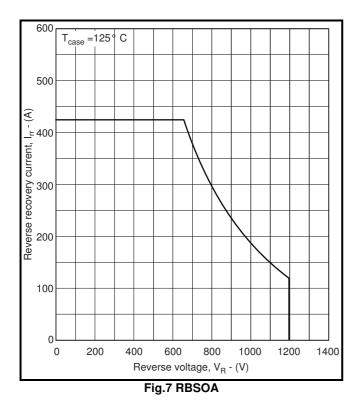
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
t <sub>rr</sub>	Reverse recovery time	I <sub>F</sub> = 300A, dI <sub>F</sub> /dt = 2250A/μs, V <sub>R</sub> = 600V	-	0.5	-	μs
I <sub>rr</sub>	Reverse recovery current		-	320	-	А
Q <sub>rr</sub>	Reverse recovery charge		-	85	-	μC
E <sub>rec</sub>	Reverse recovery energy		-	32	-	mJ





Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures

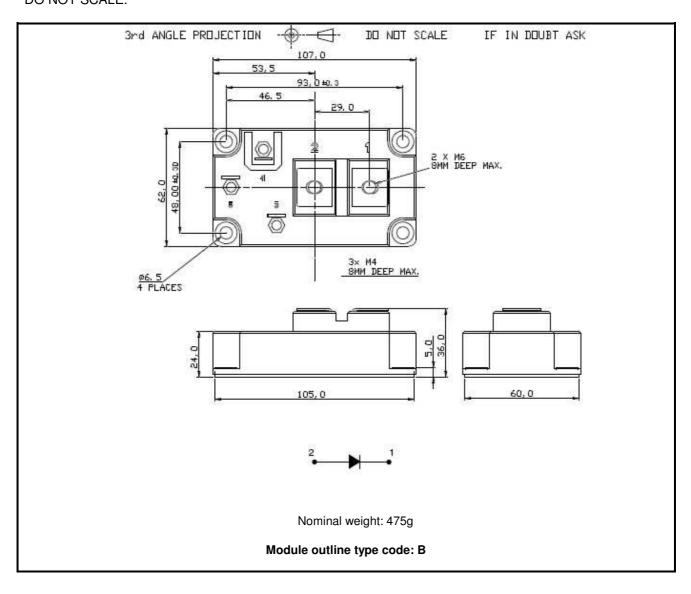






## PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





#### POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

#### HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



http://www.dynexsemi.com

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